

Application No. 10/075,464  
Reply to Office Action of October 8, 2003

IN THE SPECIFICATION

Please amend the Title on page 1 as follows:

SEMICONDUCTOR MEMORY DEVICE HAVING MIS-TYPE TRANSISTORS  
AND ITS MANUFACTURING METHOD

Please amend the paragraph at page 15, lines 29-33 to read as follows:

Furthermore, although the embodiments have been explained by way of nMOSFET or CMOSFET using the SOI substrate, the invention is not limited to it, but can use be applied to pMOSFET or other types of substrate such as pMOSFET, SOS (silicon on sapphire), and so forth.